2SB1392

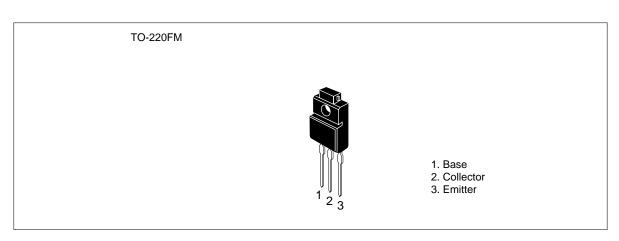
Silicon PNP Triple Diffused

HITACHI

Application

Low frequency power amplifier

Outline



Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

Item	Symbol	Ratings	Unit
Collector to base voltage	V _{CBO}	-7 0	V
Collector to emitter voltage	V _{CEO}	-60	V
Emitter to base voltage	V_{EBO}	- 5	V
Collector current	I _c	-4	A
Collector peak current	I _{C(peak)}	-8	A
Collector power dissipation	P _c	2	W
	P _C *1	25	
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

Note: 1. Value at $T_c = 25$ °C.



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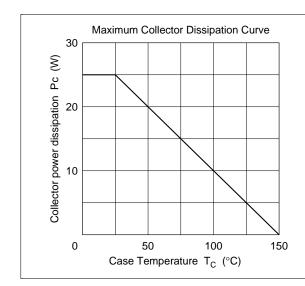
Electrical Characteristics ($Ta = 25^{\circ}C$)

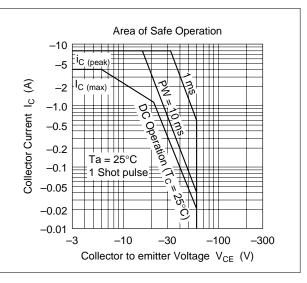
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	-70	_	_	V	$I_{c} = -10 \ \mu A, \ I_{e} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-60		_	V	$I_{\rm C}$ = -50 mA, $R_{\rm BE}$ =
Emitter to base breakdown voltage	$V_{(BR)EBO}$	- 5		_	V	$I_{E} = -10 \ \mu A, \ I_{C} = 0$
Collector cutoff current	I _{CBO}			-10	μA	$V_{CB} = -50 \text{ V}, I_{E} = 0$
	I _{CEO}	-		-10	_	$V_{CE} = -50 \text{ V}, R_{BE} =$
DC current transfer ratio	h _{FE1} *2	60	_	200		$V_{CE} = -4 \text{ V}, I_{C} = -1 \text{ A}^{*1}$
	h _{FE2}	35	_	_	_	$V_{CE} = -4 \text{ V}, I_{C} = -0.1 \text{ A}^{*1}$
Base to emitter voltage	V_{BE}	-		-1.0	V	$V_{CE} = -4 \text{ V}, I_{C} = -1 \text{ A}^{*1}$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_		-1.0	V	$I_{\rm C} = -2.0 \text{ A}, I_{\rm B} = -0.2 \text{ A}^{*1}$
Base to emitter saturation voltage	$V_{BE(sat)}$			-1.2	V	$I_{\rm C} = -2.0 \text{ A}, I_{\rm B} = -0.2 \text{ A}^{*1}$

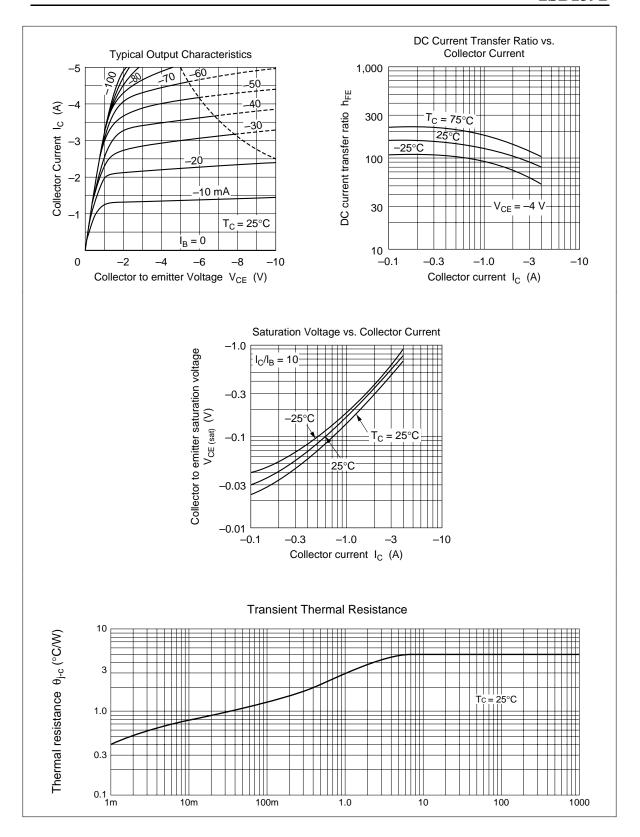
Notes: 1. Pulse test.

2. The 2SB1392 is grouped by $h_{\mbox{\tiny FE1}}$ as follows.

В	С
60 to 120	100 to 200







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